



UNISONIC TECHNOLOGIES CO., LTD

7N70

Power MOSFET

7 Amps, 700 Volts N-CHANNEL POWER MOSFET

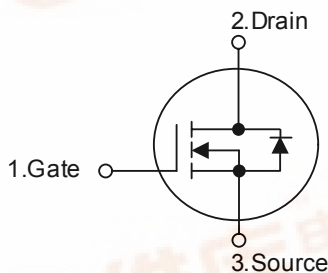
DESCRIPTION

The UTC 7N70 is a high voltage MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} = 1.5\Omega @ V_{GS} = 10V$
- * Ultra low gate charge (typical 30 nC)
- * Low reverse transfer capacitance ($C_{RSS} =$ typical 18 pF)
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

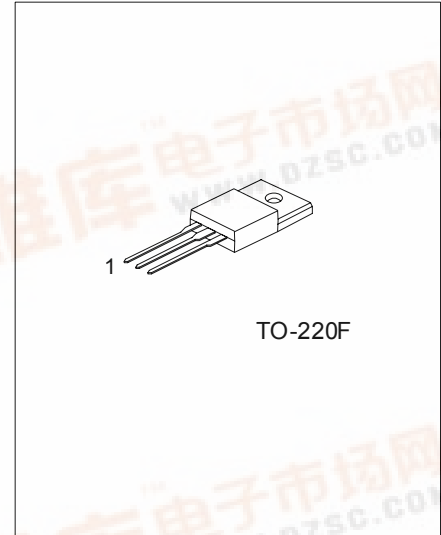
SYMBOL



ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
7N70-TF3-T	7N70L-TF3-T	TO-220F	G	D	S	Tube

7N70L-TF3-T (1)Packing Type (2)Package Type (3)Lead Plating	(1) T: Tube (2) TF3: TO-220F (3) L: Lead Free Plating Blank: Pb/Sn
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*Pb-free plating product number: 7N70L

■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	700	V
Gate-Source Voltage	V_{GSS}	± 30	V
Continuous Drain Current	I_D	$T_C = 25^\circ\text{C}$	A
		$T_C = 100^\circ\text{C}$	A
Drain Current Pulsed (Note 1)	I_{DM}	28	A
Avalanche Energy, Single Pulsed (Note 2)	E_{AS}	530	mJ
Avalanche Energy, Repetitive, Limited by T_{JMAX}	E_{AR}	14.2	mJ
Peak Diode Recovery dv/dt (Note 3)	dv/dt	4.5	V/ns
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	142	W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Junction-to-Ambient	θ_{JA}			62.5	$^\circ\text{C/W}$
Junction-to-Case	θ_{JC}			0.88	$^\circ\text{C/W}$

■ ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF Characteristics							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} = 0 V, I _D = 250 μA	700			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} = 700 V, V _{GS} = 0 V			1	μA
			V _{DS} = 560 V, T _C = 125°C			1	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
	Reverse		V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
Breakdown Voltage Temperature Coefficient		ΔBV _{DSS} /ΔT _J	I _D = 250 μA, Referenced to 25°C		0.67		V/°C
ON Characteristics							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250 μA	2.0		4.0	V
Drain-Source ON-State Resistance		R _{DS(ON)}	V _{GS} = 10 V, I _D = 3.5 A		1.35	1.5	Ω
Forward Transconductance		g _{FS}	V _{DS} = 40 V, I _D = 3.5 A (Note 4)		8.0		S
Dynamic Characteristics							
Input Capacitance		C _{ISS}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1MHz		1200	1600	pF
Output Capacitance		C _{OSS}			150	190	pF
Reverse Transfer Capacitance		C _{RSS}			18	25	pF
Switching Characteristics							
Turn-on Delay Time		t _{D(ON)}	V _{DD} = 350V, I _D = 7.0 A (Note 4, 5)		35	80	ns
Turn-on Rise Time		t _R			79	165	ns
Turn-off Delay Time		t _{D(OFF)}			80	160	ns
Turn-off Fall Time		t _F			52	120	ns
Total Gate Charge		Q _G	V _{DS} = 560V, I _D = 7.0A, V _{GS} = 10 V (Note 4, 5)		30		nC
Gate-Source Charge		Q _{GS}			6.5		nC
Gate-Drain Charge		Q _{DD}			13		nC

■ ELECTRICAL CHARACTERISTICS(Cont.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Source- Drain Diode Ratings and Characteristics						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 7.0\text{ A}$			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				7.0	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				28	A
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, I_S = 7.0\text{ A},$ $dI_F/dt = 100\text{ A}/\mu\text{s}$ (Note 4)		320		ns
Reverse Recovery Charge	Q_{RR}			2.4		μC

- Notes:
1. Repetitive Rating : Pulse width limited by T_J
 2. $L = 19.5\text{mH}$, $I_{AS} = 7.0\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 0\ \Omega$, Starting $T_J = 25^\circ\text{C}$
 3. $I_{SD} \leq 7.0\text{A}$, $di/dt \leq 100\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
 4. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
 5. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

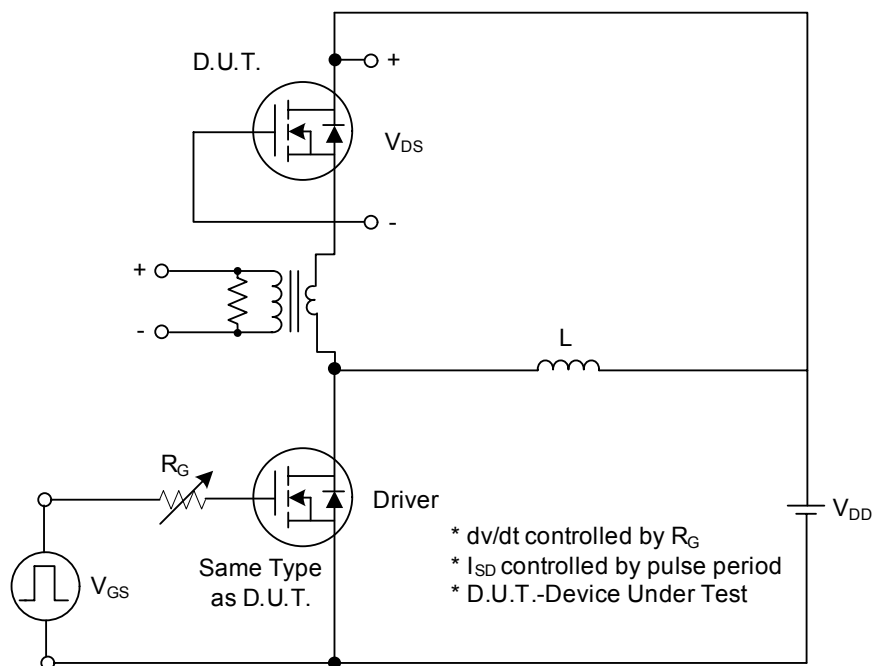


Fig. 1A Peak Diode Recovery dv/dt Test Circuit

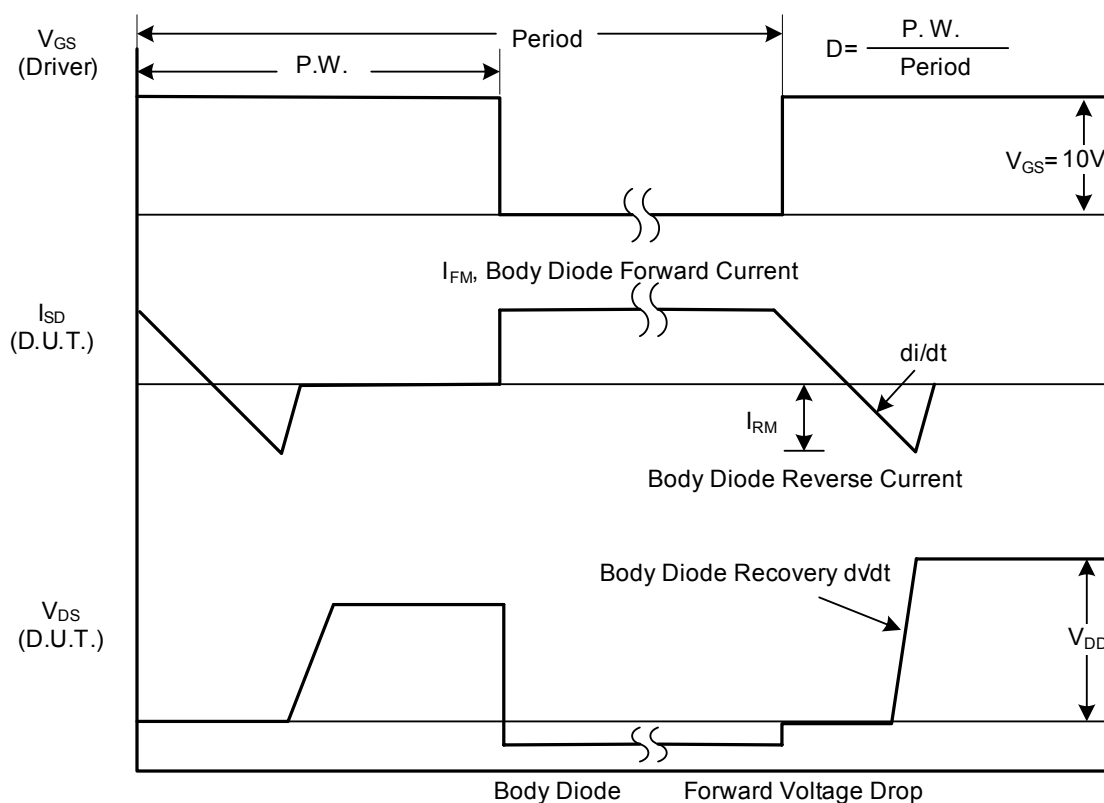


Fig. 1B Peak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS (Cont.)

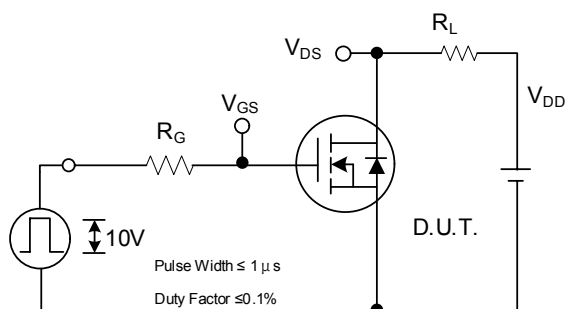


Fig. 2A Switching Test Circuit

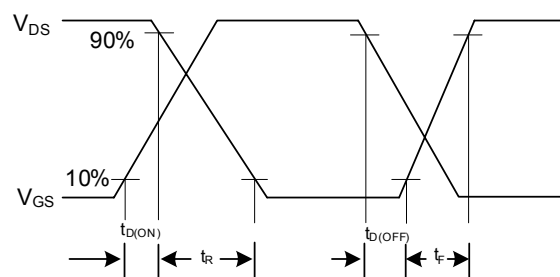


Fig. 2B Switching Waveforms

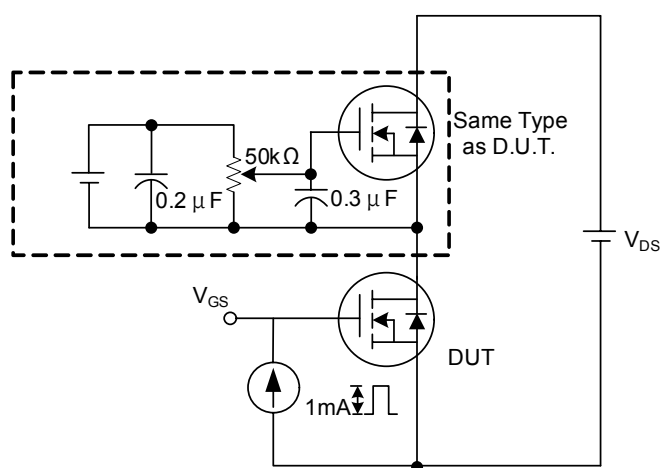


Fig. 3A Gate Charge Test Circuit

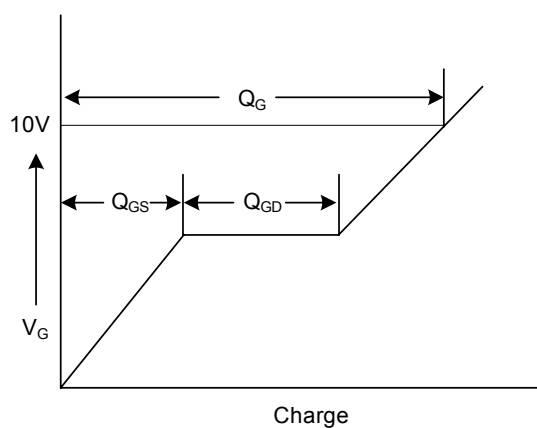


Fig. 3B Gate Charge Waveform

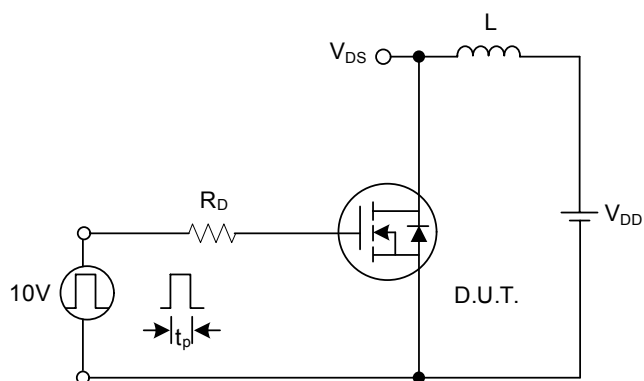


Fig. 4A Unclamped Inductive Switching Test Circuit

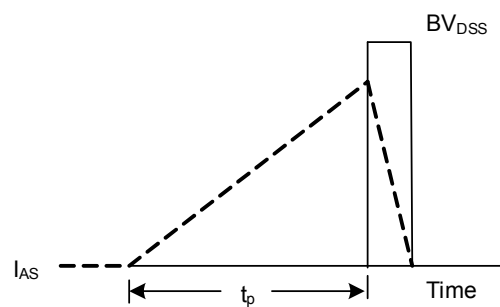
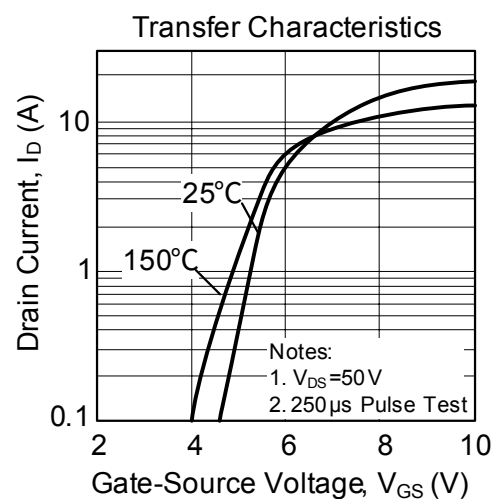
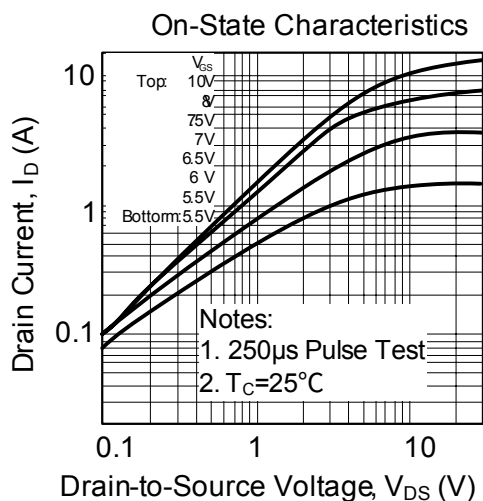
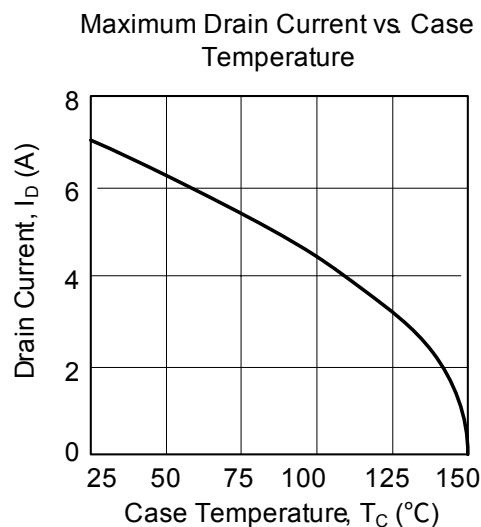
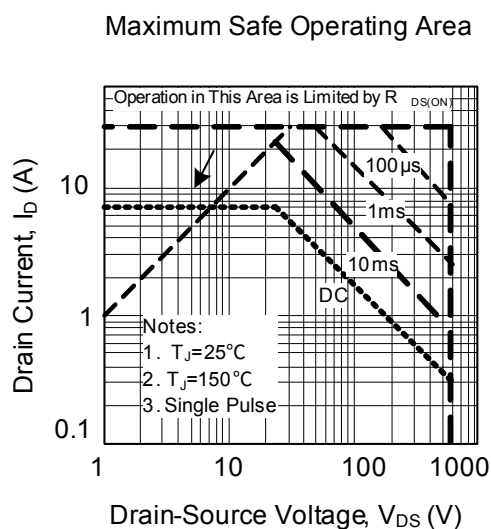
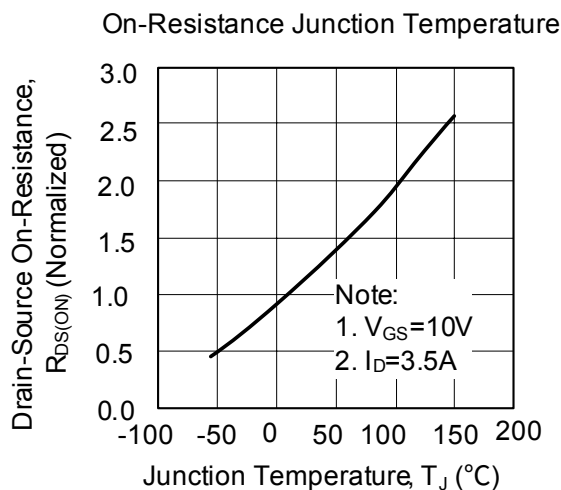
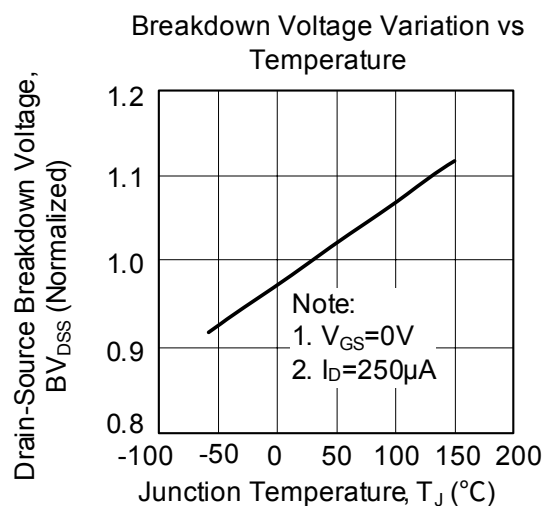


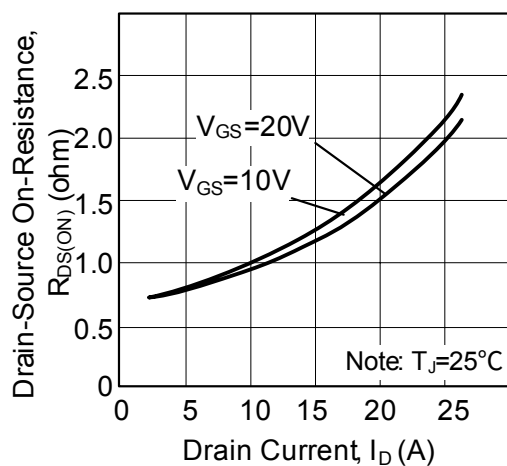
Fig. 4B Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

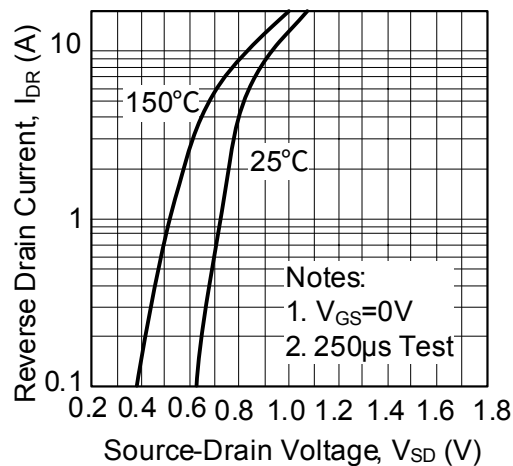


■ TYPICAL CHARACTERISTICS(Cont.)

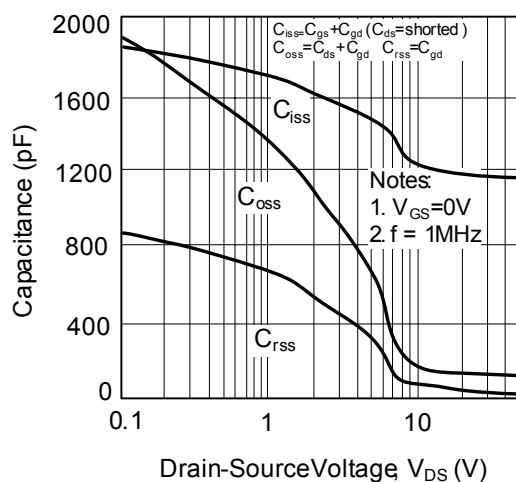
On-Resistance Variation vs Drain Current and Gate Voltage



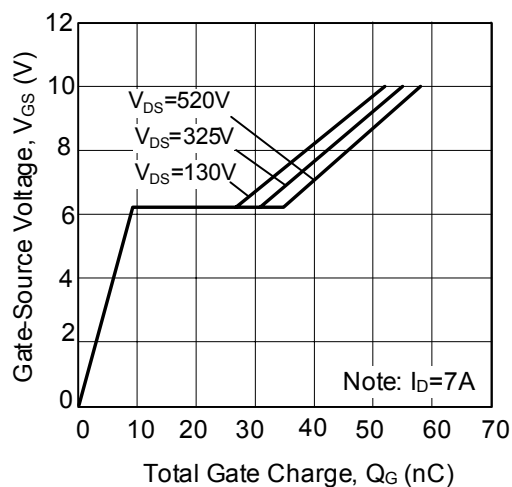
On State Current vs. Allowable Case Temperature



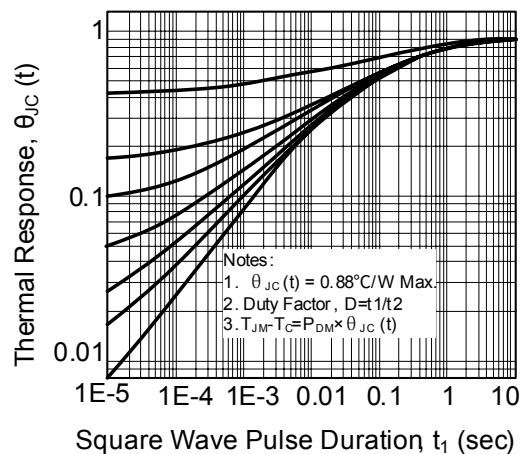
Capacitance Characteristics (Non-Repetitive)



Gate Charge Characteristics



Transient Thermal Response Curve



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